

**TENTATIVE**

TOSHIBA Photocoupler Photo-Diode

# TLP722

The TOSHIBA TLP722 consists of a photo-diode optically coupled to a gallium arsenide infrared emitting diode in a four lead plastic DIP (DIP4).

TLP722: Single circuit

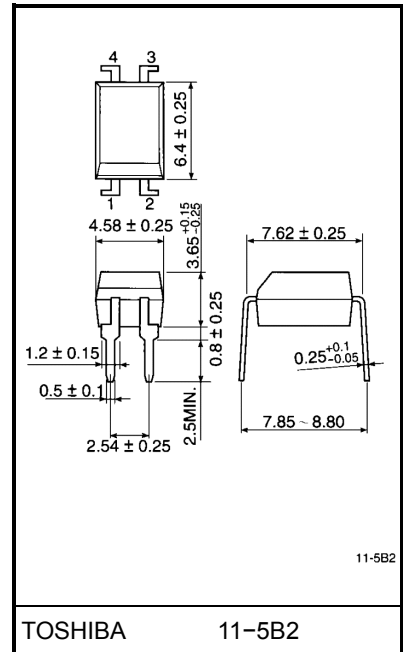
- Cathode-anode voltage: 30V (max)
- Current transfer ratio: 0.1% (min)
- Input / output isolation voltage: 4000V<sub>rms</sub> (min)
- Operating temperature range: -55~100°C
- Storage temperature range: -55~125°C
- UL recognized: UL1577, E67349
- VDE approved: VDE0884
  - Maximum operating insulation voltage: 890V<sub>PK</sub>
  - Maximum permissible over voltage: 8000V<sub>PK</sub>

**(Note): When a VDE0884 approved type is needed, please designate the " Option (D4) "**

- SEMKO approved product: SS EN60950, approved No. 9808324 / 01
- Construction mechanical rating

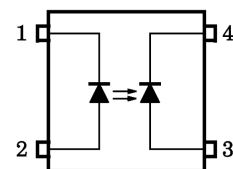
|                      | TLP722 type | TLP722F type |
|----------------------|-------------|--------------|
| Creepage distance    | 7.0 mm      | 8.0 mm       |
| Clearance            | 7.0 mm      | 8.0 mm       |
| Insulation thickness | 0.4 mm      | 0.4 mm       |

Unit in mm



Weight: 0.28 g

### Pin Configuration (top view)



- 1 : LED CATHODE
- 2 : LED ANODE
- 3 : DETECTOR ANODE
- 4 : DETECTOR CATHODE

## Maximum Ratings (Ta = 25°C)

| Characteristic                    |                           | Symbol                        | Rating                        | Unit      |
|-----------------------------------|---------------------------|-------------------------------|-------------------------------|-----------|
| LED                               | Forward current           | $I_F$                         | 25                            | mA        |
|                                   | Forward current derating  | $\Delta I_F / ^\circ\text{C}$ | -0.45<br>(Ta ≥ 70°C)          | mA / °C   |
|                                   | Pulse forward current     | $I_{FP}$                      | 1<br>(1μs pulse, 1000 pps)    | mA        |
|                                   | Pulse forward current     | $I_{FTP}$                     | 1<br>(100μs pulse, 1000 pps)  | A         |
|                                   | Reverse voltage           | $V_R$                         | 5                             | V         |
| Detector                          | Cathode-anode voltage     | $V_{KAO}$                     | 30                            | V         |
|                                   | Anode-cathode voltage     | $V_{AKO}$                     | 0.5                           | V         |
|                                   | Photodiode output current | $I_{PB}$                      | 100                           | μA        |
|                                   | Junction temperature      | $T_j$                         | 125                           | °C        |
| Storage temperature range         |                           | $T_{stg}$                     | -55~125                       | °C        |
| Operating temperature range       |                           | $T_{opr}$                     | -55~100                       | °C        |
| Lead soldering temperature (10 s) |                           | $T_{sol}$                     | 260 (10s)                     | °C        |
| Isolation voltage                 |                           | $BV_S$                        | 4000<br>(AC, 1min., R.H. 60%) | $V_{rms}$ |

## Individual Electrical Characteristics (Ta = 25°C)

| Characteristic |                                 | Symbol                     | Test Condition                                  | Min | Typ. | Max  | Unit |
|----------------|---------------------------------|----------------------------|---|-----|------|------|------|
| LED            | Forward voltage                 | $V_F$                      | $I_F = 16 \text{ mA}$                           | —   | 1.65 | 1.85 | V    |
|                | Reverse current                 | $I_R$                      | $V_R = 5 \text{ V}$                             | —   | —    | 10   | μA   |
|                | Capacitance                     | $C_T$                      | $V = 0, f = 1 \text{ MHz}$                      | —   | 30   | —    | pF   |
| Detector       | Cathode-anode breakdown voltage | $V_{(BR)KAO}$              | $I_{KA} = 0.1 \text{ mA}$                       | 30  | —    | —    | V    |
|                | Anode-cathode breakdown voltage | $V_{(BR)AKO}$              | $I_{AK} = 0.1 \text{ mA}$                       | 0.5 | —    | —    | V    |
|                | Dark current                    | $I_{leak}$                 | $V_{KA} = 10 \text{ V}$                         | —   | —    | 50   | nA   |
|                |                                 |                            | $V_{KA} = 10 \text{ V}, T_a = 85^\circ\text{C}$ | —   | —    | 1    | μA   |
|                | Photodiode output current       | $I_{PB}$                   | $V = 10 \text{ mA}, V_{KA} = 5 \text{ V}$       | 10  | —    | 50   | μA   |
| Capacitance    | $C_{AK}$                        | $V = 0, f = 1 \text{ MHz}$ | —   | 10  | —    | pF   |      |

## Isolation Characteristics (Ta = 25°C)

| Characteristic                | Symbol | Test Condition               | Min                | Typ.      | Max | Unit      |
|-------------------------------|--------|------------------------------|--------------------|-----------|-----|-----------|
| Capacitance (input to output) | $C_S$  | $V_S = 0, f = 1 \text{ MHz}$ | —                  | 0.8       | —   | pF        |
| Isolation resistance          | $R_S$  | $V_S = 500 \text{ V}$        | $1 \times 10^{12}$ | $10^{14}$ | —   | Ω         |
| Isolation voltage             | $BV_S$ | AC, 1 minute                 | 4000               | —         | —   | $V_{rms}$ |
|                               |        | AC, 1 second, in oil         | —                  | 10000     | —   |           |
|                               |        | DC, 1 minute, in oil         | —                  | 10000     | —   | $V_{dc}$  |

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